

# DMN3042L-13 Datasheet



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DiGi Electronics Part Number	DMN3042L-13-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	DMN3042L-13
Description	MOSFET N-CH 30V 5.8A SOT23
Detailed Description	N-Channel 30 V 5.8A (Ta) 720mW (Ta) Surface Mount SOT-23-3



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## Purchase and inquiry

Manufacturer Product Number:

DMN3042L-13

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

2.5V, 10V

Vgs(th) (Max) @ Id:

1.4V @ 250 $\mu$ A

Vgs (Max):

$\pm$ 12V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-23-3

Base Product Number:

DMN3042

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

5.8A (Ta)

Rds On (Max) @ Id, Vgs:

26.5mOhm @ 5.8A, 10V

Gate Charge (Qg) (Max) @ Vgs:

20 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

860 pF @ 15 V

Power Dissipation (Max):

720mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-236-3, SC-59, SOT-23-3

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ max
30V	26.5m $\Omega$ @ $V_{GS} = 10V$	5.8A
	32m $\Omega$ @ $V_{GS} = 4.5V$	5.0A

## Features and Benefits


- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery charging
- Power management functions
- DC-DC converters
- Portable power adaptors

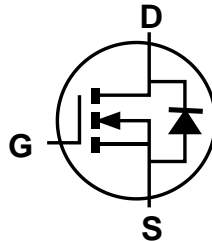
## Mechanical Data

- Package: SOT23 (Standard)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

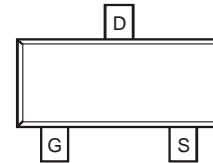
SOT23 (Standard)



Top View



Internal Schematic



Top View

## Ordering Information

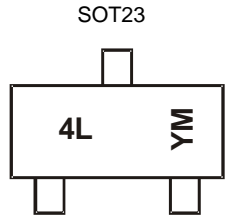
Part Number	Package	Packing	
		Qty.	Carrier
DMN3042L-7	SOT23 (Standard)	3,000	Tape & Reel
DMN3042L-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.



DMN3042L

## Marking Information



4L = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2017	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	E	.....	I	J	K	L	M	N	O	P	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V	
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	$I_D$	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	5.8 4.0	A
Maximum Body Diode Forward Current (Note 6)		$I_S$	1.5	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)	$I_{DM}$	30	A	

## Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)	$P_D$	0.72	W	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady State	171	$^\circ\text{C/W}$
Power Dissipation (Note 6)		$P_D$	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady State	93	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

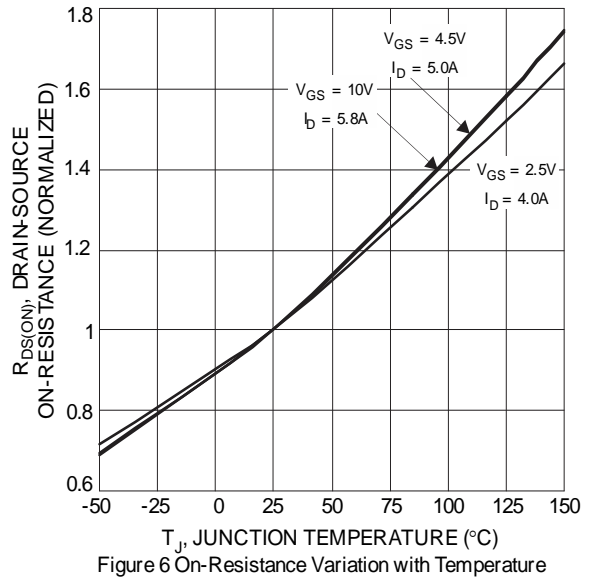
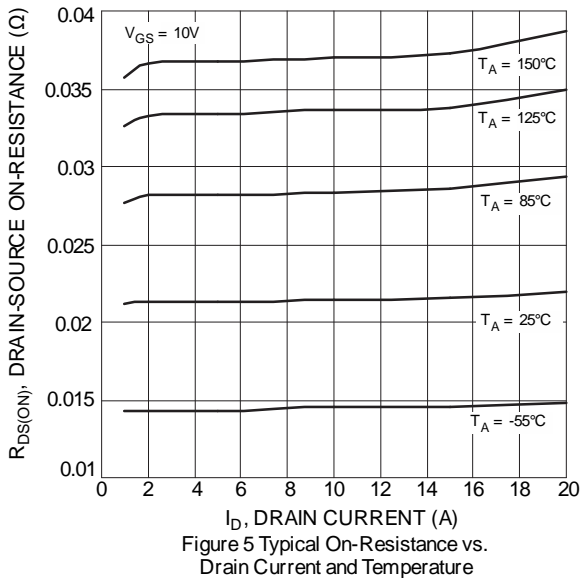
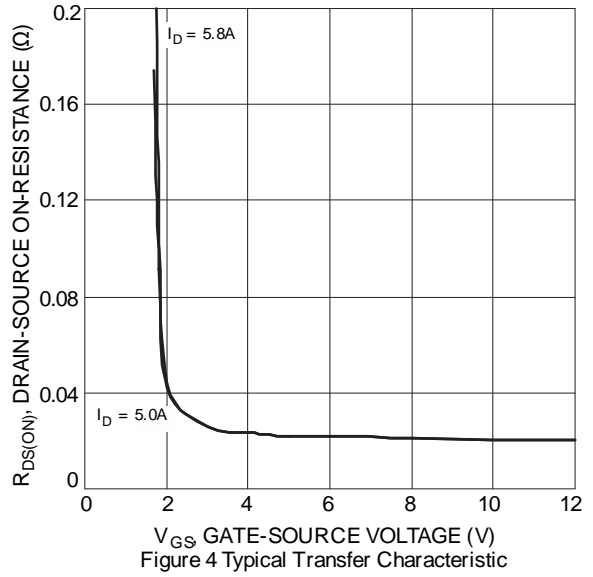
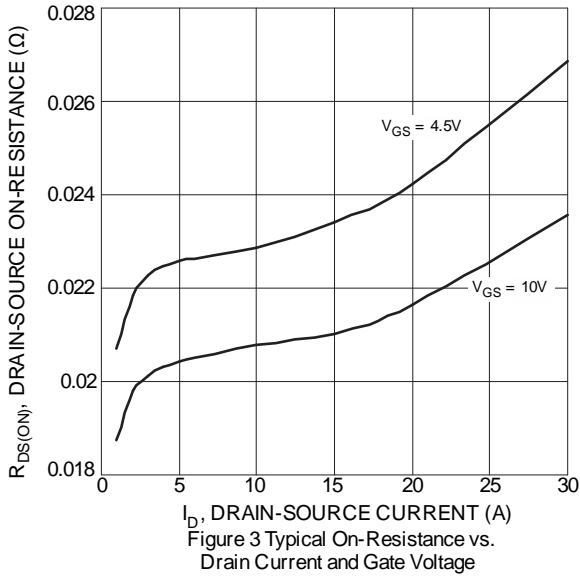
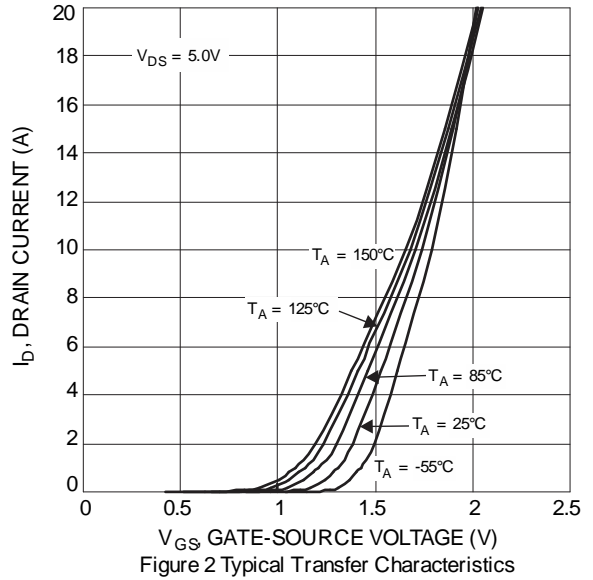
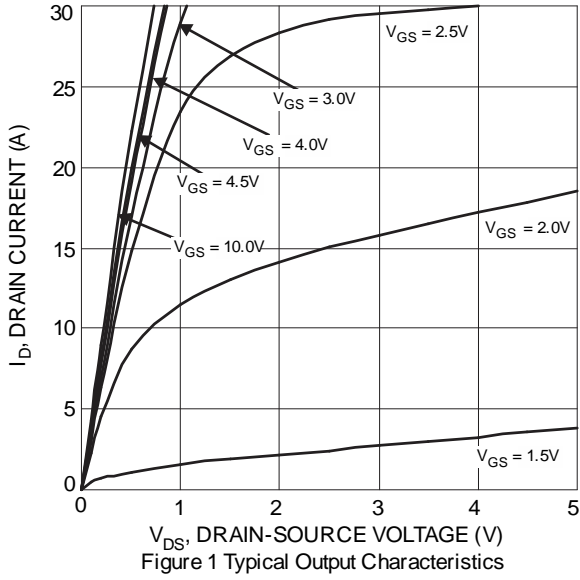

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$  unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	21	26.5	m $\Omega$	$V_{GS} = 10V, I_D = 5.8A$
		—	23	32		$V_{GS} = 4.5V, I_D = 5.0A$
		—	29	48		$V_{GS} = 2.5V, I_D = 4.0A$
Diode Forward Voltage	$V_{SD}$	—	0.7	1.2	V	$V_{GS} = 0V, I_S = 1A$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	570	860	pF	$V_{DS} = 15V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	63	95		
Reverse Transfer Capacitance	$C_{rss}$	—	53	80		
Gate Resistance	$R_G$	—	3.2	4.5	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge ( $V_{GS} = 10V$ )	$Q_g$	—	13.3	20	nC	$V_{DS} = 15V, I_D = 6.9A$
Total Gate Charge ( $V_{GS} = 4.5V$ )	$Q_g$	—	6.1	8		
Gate-Source Charge	$Q_{gs}$	—	1.0	1.5		
Gate-Drain Charge	$Q_{gd}$	—	1.6	2.5		
Turn-On Delay Time	$t_{D(on)}$	—	1.5	2.4	nS	$V_{GS} = 10V, V_{DD} = 15V, R_G = 3\Omega,$ $I_D = 6.9A$
Turn-On Rise Time	$t_r$	—	3.3	5		
Turn-Off Delay Time	$t_{D(off)}$	—	13.9	22		
Turn-Off Fall Time	$t_f$	—	4.9	7		
Body Diode Reverse Recovery Time	$t_{rr}$	—	7.8	12	nS	$I_S = 5A, dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{rr}$	—	1.9	3	nC	$I_S = 5A, dI/dt = 100A/\mu s$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



**DMN3042L**





**DMN3042L**

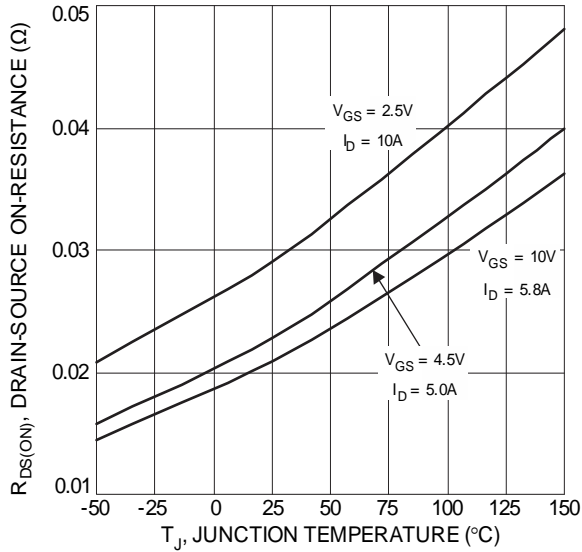


Figure 7 On-Resistance Variation with Temperature

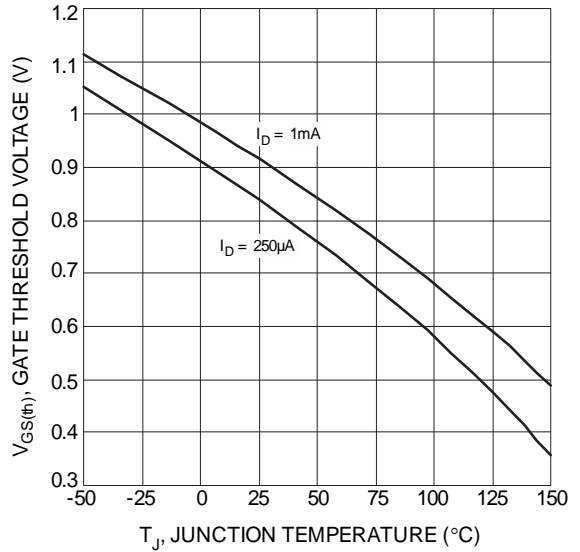


Figure 8 Gate Threshold Variation vs. Ambient Temperature

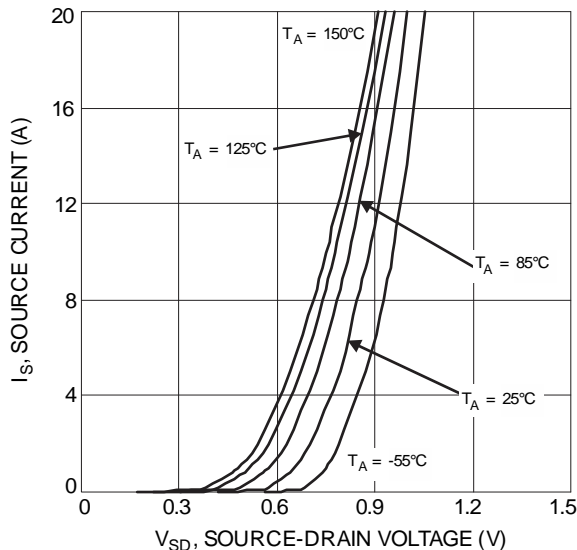


Figure 9 Diode Forward Voltage vs. Current

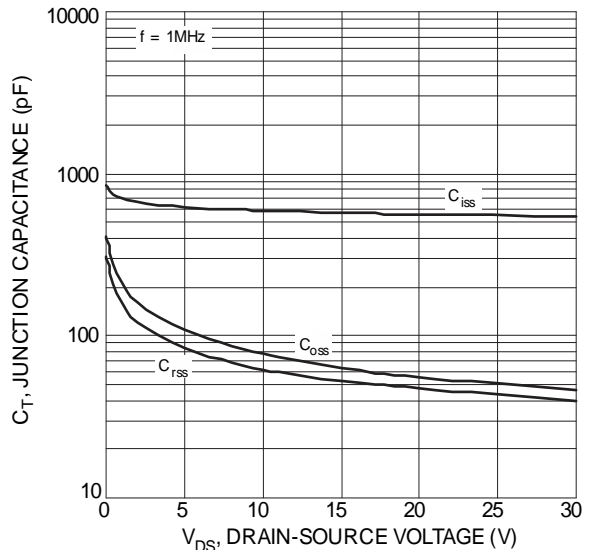


Figure 10 Typical Junction Capacitance

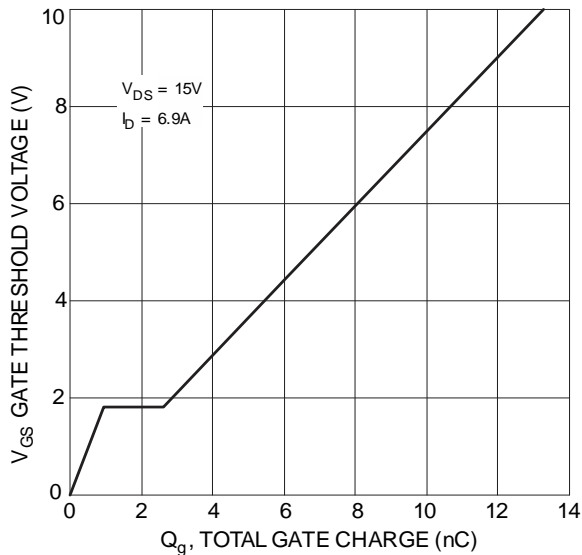


Figure 11 Gate Charge

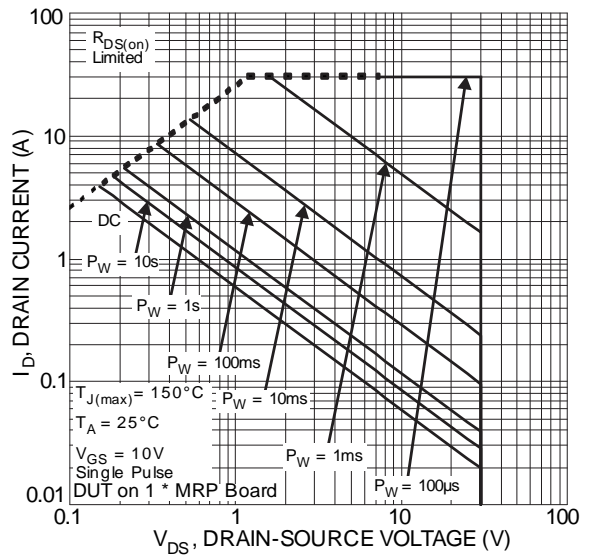
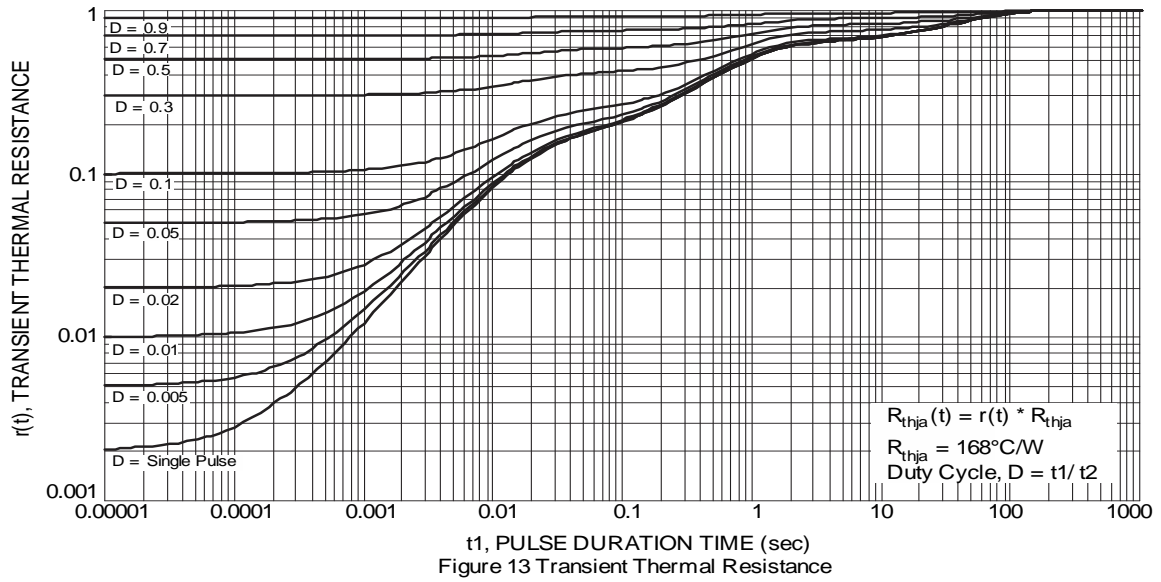


Figure 12 SOA, Safe Operation Area



DMN3042L

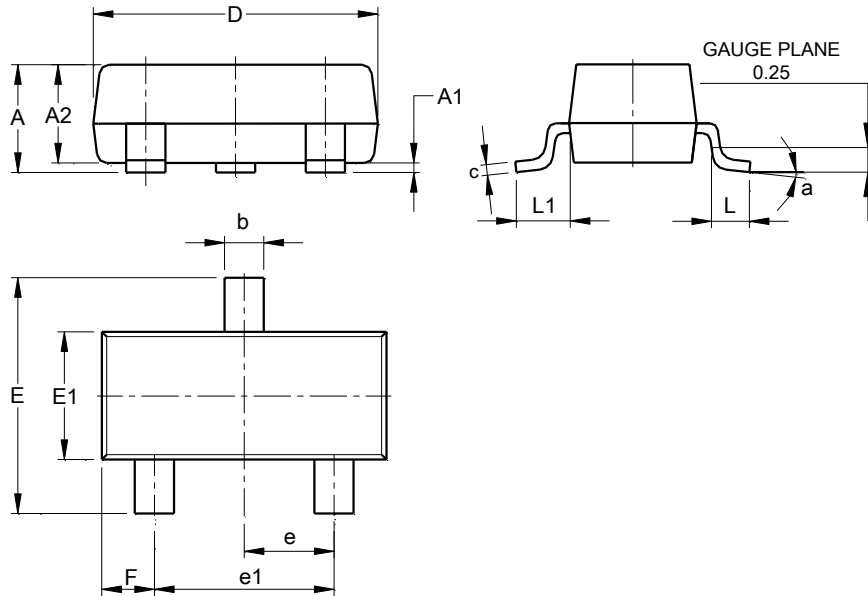




## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

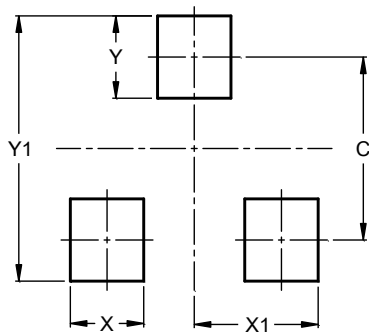
### SOT23 (Standard)



SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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